PNP Epitaxial Planar Silicon High Voltage Transistor, 150VcEO, 600mA Ic





RoHS Compliant

PNP



Absolute Max. Ratings Ta=25°C unless otherwise noted

Parameter	Symbol	Value	Units			
Collector-Emitter Voltage	VCEO	150	V			
Collector-Base Voltage	Vсво	160	V			
Emitter-Base Voltage	Vево	5	V			
Collector Current Continuous	Ic	600	mA			
Power Dissipation @T _A = 25°C Derate Above 25°C	Po	625 5	mW mW/°C			
Power Dissipation @Tc = 25°C Derate Above 25°C	Po	1.5 12	W mW/°C			
Operating and Storage Junction Temperature Range	Т _J , Тsтg	-55 to +150	°C			
Thermal Resistance						
Junction to Case	Rth(j-c)	83.3	°C/W			
Junction to Ambient	Rth(j-a)	200	°C/W			

Electrical Characteristics T_A = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Туре	Max.	Units
Collector -Emitter Voltage	Vceo*	Ic = 1mA, IB = 0	150	-	1	V
Collector -Base Voltage	Vсво	Ic = 100μA, Iε = 0	160	-	-	V
Emitter -Base Voltage	VEBO	I _E = 10μA, I _C = 0	5	-	-	V
Collector-Cut off Current	Ісво	V _{CB} = 160V, IE = 0	-	-	50	nA
Emitter Cut-off Current	ІЕВО	TA = 100°C VCB = 160V, IE = 0 VEB = 4V, IC = 0	- -	- -	50 50	μA nA
DC Current Gain	hFE*	Ic = 1mA, VCE = 5V Ic = 10mA, VCE = 5V Ic = 50mA, VCE = 5V	50 60 50	- - -	- 240 -	
Collector Emitter Saturation Voltage	Vce(sat)*	Ic = 10mA, I _B = 1mA Ic = 50mA, I _B = 5mA	- -	-	0.2 0.5	V
Base Emitter Saturation Voltage	VBE(sat)*	Ic = 10mA, Iв = 1mA Ic = 50mA, Iв = 5mA	- -	-	1.0 1.0	V

^{*}Pulse Test: Pulse Width = 300µs, Duty Cycle = 2% T

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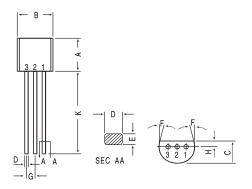
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Dynamic Characteristics

Parameter	Symbol	Test Condition	Min.	Type	Max.	Units
Small Signal Current Gain	hfe	Ic = 1mA, VcE = 10V, f = 1kHz	40	-	200	
Transition Frequency	ft	Vce = 10V, Ic = 10mA, f = 100MHz	100	-	300	MHz
Output Capacitance	Cobo	Vcb = 10V, IE = 0, f = 1MHz	-	-	6	pF
Noise Figure	NF	Vce = SV, Ic = 250μA R = 1kΩ, f = 10Hz to 15.7kHz	-	-	8	dB

TO-92 Plastic Package



PIN CONFIGURATION

- 1. COLLECTOR 2. BASE
- 3. EMITTER

Dim.	Min. Max.		
Α	4.32	5.33	
В	4.45	5.2	
С	3.18	4.19	
D	0.41	0.55	
Е	0.35	0.5	
F	5 Deg.		
G	1.14	1.4	
Н	1.14	1.53	
K	12.7	-	

Dimensions: Millimetres

Part Number Table

Description	Part Number	
PNP Epitaxial Planar Silicon High Voltage Transistor, 150V, 600mA,TO-92	MP001172	

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